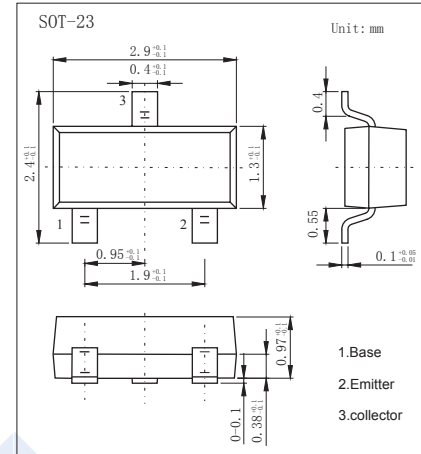


NPN Transistors

2SC4852

■ Features

- Collector Current Capability $I_c=100\text{mA}$
- Collector Emitter Voltage $V_{CE0}=15\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	25	V
Collector - Emitter Voltage	V_{CE0}	15	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_c	100	mA
Collector Current - Pulse	I_{CP}	200	
Base Current	I_B	20	
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = 100 \mu\text{A}, I_E = 0$	25			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = 1 \text{mA}, I_B = 0$	15			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu\text{A}, I_c = 0$	5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 15 \text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4 \text{V}, I_c = 0$			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = 10 \text{mA}, I_B = 1 \text{mA}$			0.03	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = 10 \text{mA}, I_B = 1 \text{mA}$			1.1	
DC current gain	h_{FE}	$V_{CE} = 2 \text{V}, I_c = 5 \text{mA}$	800		3200	
On resistance	R_{on}	$I_B = 3 \text{mA}, f = 1 \text{MHz}$		0.9		Ω
Collector output capacitance	C_{ob}	$V_{CB} = 10 \text{V}, f = 1 \text{MHz}$		1.4		pF
Transition frequency	f_t	$V_{CE} = 5 \text{V}, I_c = 10 \text{mA}$		240		MHz

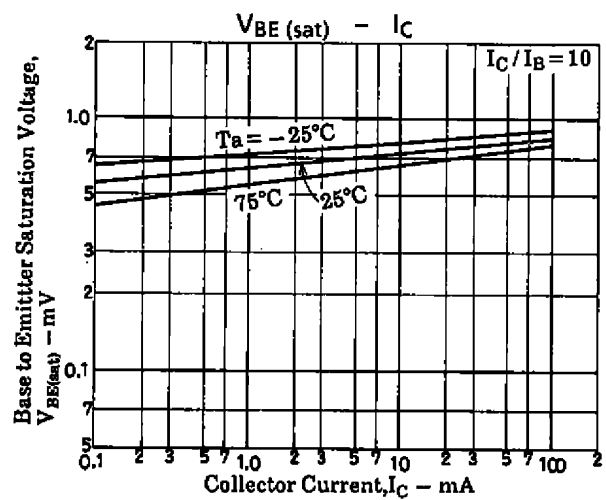
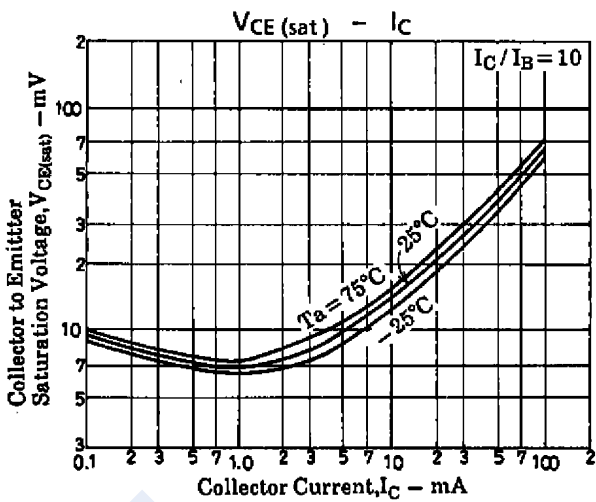
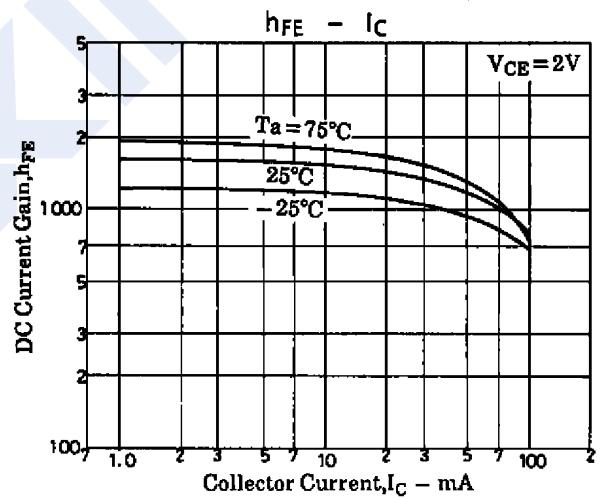
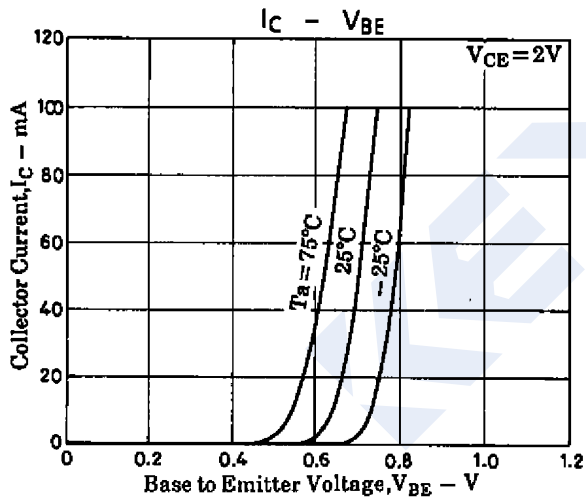
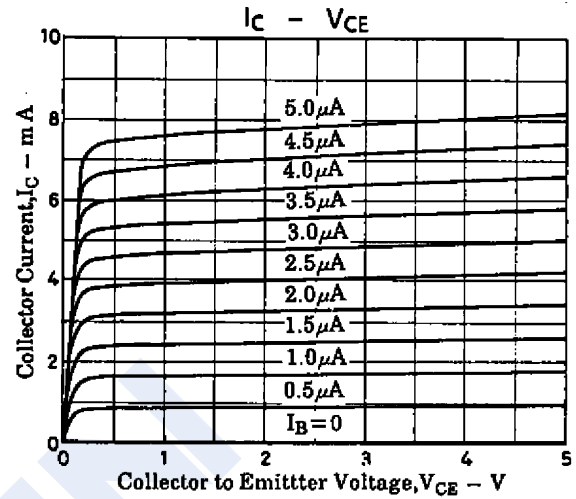
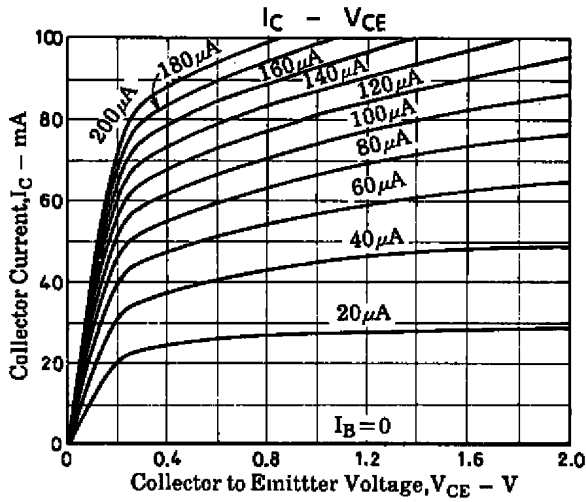
■ Marking

Marking	YT

NPN Transistors

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■ Typical Characteristics



NPN Transistors

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■ Typical Characteristics

